

In the Claims

Please cancel Claims 4 and 11-20.

Please amend Claims 1 and 5 and follows:

1. (Three times amended) An electrostatic discharge (ESD) protection structure for protecting an integrated circuit comprising:
- a first semiconductor region of a first conductivity type;
  - a second semiconductor region of a second conductivity type in contact with said first semiconductor region;
  - an electrically floating third semiconductor region of said first conductivity type in contact with said second semiconductor region and separated from said first semiconductor region by said second semiconductor region;
  - a fourth semiconductor region of said second conductivity type in contact with said third semiconductor region and separated from said second semiconductor region by said third semiconductor region; and
  - a fifth semiconductor region of said first conductivity type in contact with said fourth semiconductor region and separated from said third semiconductor region by said fourth semiconductor region; wherein a first terminal, A, of said ESD structure is connected to said first semiconductor region and said second conductor region and a second terminal, K, of said ESD structure is connected to said fourth semiconductor region and said fifth semiconductor region.

LAW OFFICES OF  
SKJERVEN MORRILL  
MACPHERSON LLP

25 METRO DRIVE  
SUITE 700  
SAN JOSE, CA 95110  
(408) 453-9200  
FAX (408) 453-7979

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5. (Amended) The ESD structure of Claim 1 wherein said third semiconductor region includes an n-well region formed in a p-type semiconductor substrate.

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LAW OFFICES OF  
SKJERVEN MORRILL  
MACPHERSON LLP

25 METRO DRIVE  
SUITE 700  
SAN JOSE, CA 95110  
(408) 453-9200  
FAX (408) 453-7979